

Form PTO-1449 (modified) List of Patents and Publications For Applicant's Information Disclosure Statement (Use several sheets if necessary)				ATTY. DOCKET NO. MCRO:199--3/FLE (95-0057.03)		SERIAL NO. 09/901,837 Unassigned	
				APPLICANT Shubneesh Batra et al.			
				FILING DATE Herewith		GROUP Unassigned 2825	

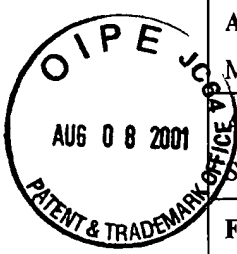
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U.S. PATENT DOCUMENTS							
EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CME	A1	4,742,014	05/03/88	Hooper et al.	437	192	05/10/85
CME	A2	4,758,533	07/19/88	Magee et al.	437	173	09/22/87
CME	A3	4,811,067	03/07/89	Fitzgerald et al.	357	23.6	05/02/86
CME	A4	4,970,176	11/13/90	Tracy et al.	437	187	09/29/89
CME	A5	4,985,750	01/15/91	Hoshino	357	71	09/17/87
CME	A6	5,019,533	05/28/91	Cuddihy et al.	437	199	05/26/89
CME	A7	5,169,803	12/08/92	Miyakawa	437	197	11/27/91
CME	A8	5,266,521	11/30/93	Lee et al.	437	188	01/31/92
CME	A9	5,293,053	03/08/94	Malhi et al.	257	330	05/01/91
CME	A10	5,312,774	05/17/94	Nakamura et al.	437	192	12/03/92
CME	A11	5,324,973	06/28/94	Sivan	257	330	05/03/93
CME	A12	5,350,712	09/27/94	Shibata	437	195	09/16/93
CME	A13	5,358,616	10/25/94	Ward	204	192.15	02/17/93
CME	A14	5,360,524	11/01/94	Hendel et al.	204	192.25	04/13/93
CME	A15	5,534,463	07/09/96	Lee et al.	437	195	01/25/93
CME	A16	5,567,243	10/22/96	Foster et al.	118	730	06/06/95
CME	A17	5,571,749	11/05/96	Matsuda et al.	437	113	12/28/94
CME	A18	5,691,571	11/25/97	Hirose et al.	257	751	12/26/95
CME	A19	5,751,064	05/12/98	Bryant et al.	257	752	03/03/95
CME	A20	5,831,335	11/03/98	Miyamoto	257	757	01/24/96
CME	A21	5,846,877	12/08/98	Kim	438	625	12/08/95
CME	A22	5,856,706	01/05/99	Lee	257	758	11/13/95
CME	A23	5,869,902	02/09/99	Lee et al.	257	773	03/11/96
CME	A24	5,880,023	03/09/99	Jun	438	652	01/05/96

FOREIGN PATENT DOCUMENTS							
EXAM. INT.	REF. DES.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION
OTHER ART (Author, Title, Journal, Volume, Pertinent Pages, & Date)							
<i>CME</i>	B1	K. Kikuta, et al., "Al-Ge Reflow Sputtering for Submicron-Contact-Hole Filling," 1991, Proc. 8 th International IEEE VLSI Multilevel Interconnection Conf., pgs. 163-169.					
<i>CME</i>	B2	K. Hirose et al., "Surface Melting Model for Al Reflow into Submicron Contact-holes and Vias," 1994, IEEE, pgs. 557-560.					
<i>CME</i>	B3	K. Kikuta et al., "Aluminum-Germanium-Copper Multilevel Damascene Process using Low Temperature Reflow Sputtering and Chemical Mechanical Polishing," 1994, IEEE, pgs. 101-104.					
<i>CME</i>	B4	I.S. Park et al., "A Novel Al-Reflow Process Using Surface Modification by the ECR Plasma Treatment and Its Application to the 256Mbit DRAM," 1994, IEEE, pgs. 109-112.					
EXAMINER <i>C. Juchart</i>				DATE CONSIDERED <i>8-17-02</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Information Disclosure Statement--PTO-1449 (Modified)

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		APPLICANT Shubneesh Batra et al.	
		FILING DATE July 10, 2001	GROUP <i>2825</i> Unassigned

U.S. PATENT DOCUMENTS

EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>CME</i>	A1	5,719,446	02/17/98	Taguchi et al.	257	751	02/12/97
<i>CME</i>	A2	5,897,370	04/27/99	Joshi et al.	438	632	10/28/96

FOREIGN PATENT DOCUMENTS

EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION

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EXAMINER <i>C. Jureskash</i>	DATE CONSIDERED <i>8-17-02</i>
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